### **Description**

The DMTH4014LPSWQ-13 uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **General Features**

 $V_{DS} = 40V I_{D} = 40A$ 

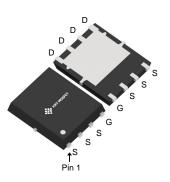
 $R_{DS(ON)} < 14m\Omega$   $V_{GS}=10V$ 

## **Application**

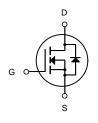
Battery protection

Load switch

Uninterruptible power supply



DFN5X6-8L



N-Channel MOSFET

**Package Marking and Ordering Information** 

Product ID	Pack	Brand	Qty(PCS)
DMTH4014LPSWQ-13	DFN5X6-8L	HXY MOSFET	5000

### Absolute Maximum Ratings (Tc=25 ℃ unless otherwise noted)

Symbol	Parameter	Rating	Units		
V <sub>DS</sub>	Drain-Source Voltage	n-Source Voltage 40			
Vgs	Gate-Source Voltage	±20	V		
Io@Tc=25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	40	Α		
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, Vos @ 10V1	28	Α		
Ірм	Pulsed Drain Current <sup>2</sup>	160	Α		
EAS	Single Pulse Avalanche Energy <sup>3</sup>	50	mJ		
Тѕтс	Storage Temperature Range	Storage Temperature Range -55 to 175			
TJ	Operating Junction Temperature Range	-55 to 175	°C		

### N-Channel Enhancement Mode MOSFET

## Electrical Characteristics (T<sub>C</sub>=25 ℃ unless otherwise noted)

Parameter	Symbol	Ol Condition		Тур	Max	Unit	
Off Characteristics	·						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	40	-	-	V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	-	-	1	μA	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA	
On Characteristics (Note 3)			•	•			
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	1	1.6	2.5	V	
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	-	11	14	mΩ	
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =20A	30	-	-	S	
Dynamic Characteristics (Note4)	·						
Input Capacitance	C <sub>Iss</sub>	\/ -05\/\/ -0\/	-	1540	-	PF	
Output Capacitance	Coss	$V_{DS}$ =25V, $V_{GS}$ =0V, F=1.0MHz	-	171	-	PF	
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHZ	-	115	-	PF	
Switching Characteristics (Note 4)			•	•			
Turn-on Delay Time	t <sub>d(on)</sub>		-	5.0	-	nS	
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}=20V, I_{D}=20A, R=1\Omega$	-	24	-	nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{GEN}$ =3 $\Omega$	-	38	-	nS	
Turn-Off Fall Time	t <sub>f</sub>		-	12	-	nS	
Total Gate Charge	Qg	\/ -20\/ L -20A	-	24	-	nC	
Gate-Source Charge	$Q_{gs}$	$V_{DS}$ =30V, $I_{D}$ =30A, $V_{GS}$ =10V	-	5.9	-	nC	
Gate-Drain Charge	$Q_{gd}$	VGS-10V	-	3.6	-	nC	
Drain-Source Diode Characteristics				•			
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =30A	-	-	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	40	Α	
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF =30A	-	9		nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	15		nC	
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)					

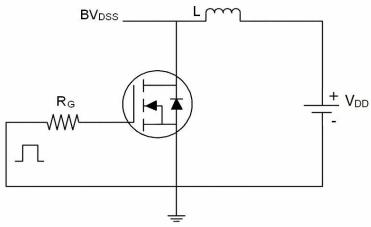
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- **5.**  $E_{AS}$  condition:  $Tj=25^{\circ}C$ , $V_{DD}=30V$ , $V_{G}=10V$ ,L=0.5mH, $Rg=25\Omega$

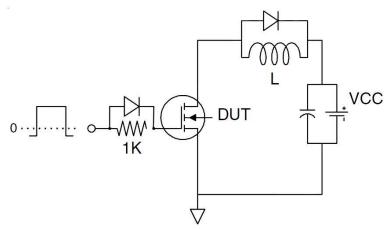


## **Test circuit**

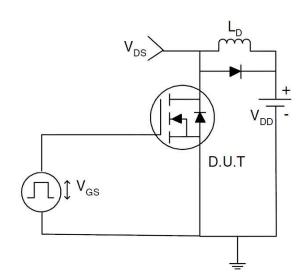
## 1) E<sub>AS</sub> test Circuits



## 2) Gate charge test Circuit

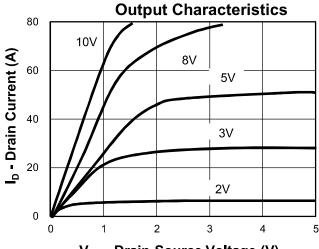


## 3) Switch Time Test Circuit





## **Typical Performance Characteristics**





2.5

2.0

1.5

1.0

0.5

0.0

-50

-25

Normalized On Resistance

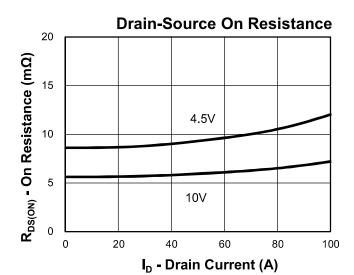
V<sub>GS</sub>=10V I<sub>DS</sub>=40A

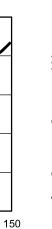
**Drain-Source On Resistance** 

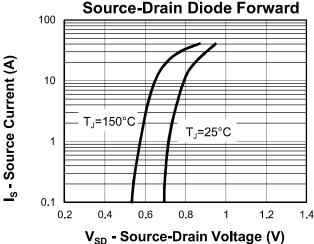
T<sub>1</sub>=25°C Rds(on)=5.5m $\Omega$ 

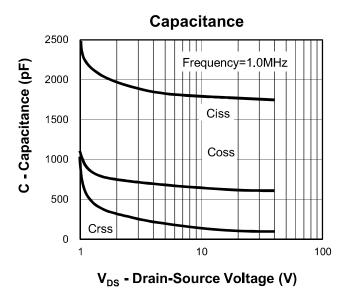
100

125







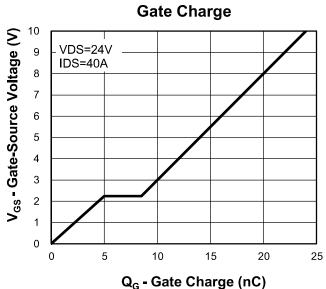


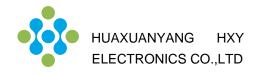
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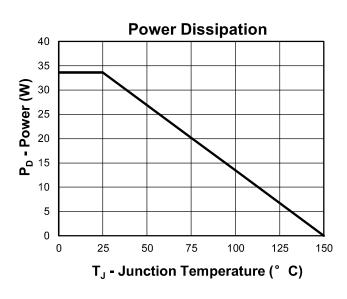
50

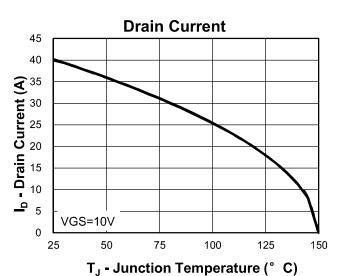
T<sub>.1</sub> - Junction Temperature (° C)

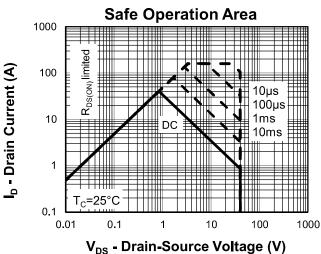
75

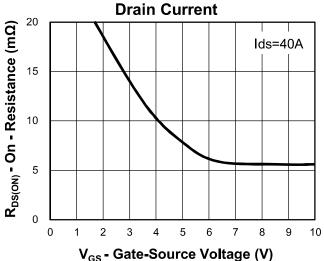




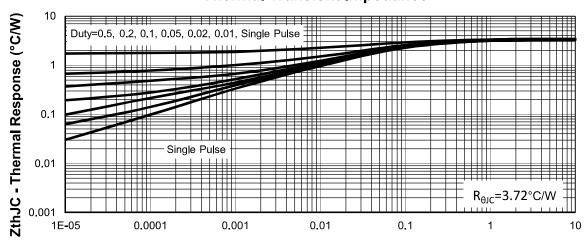








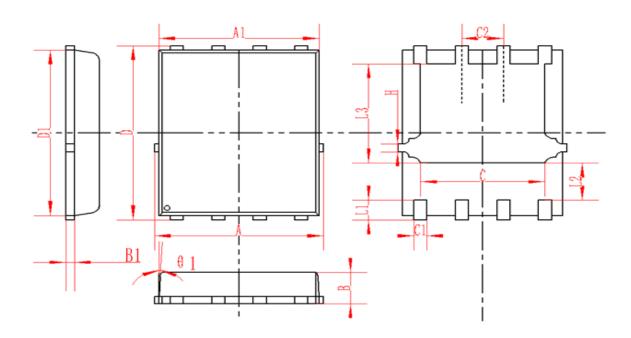
## **Thermal Transient Impedance**



**Square Wave Pulse Duration (sec)** 

## N-Channel Enhancement Mode MOSFET

# **DFN5X6-8L Package Information**



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1		0.254REF			0.010REF	
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010



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